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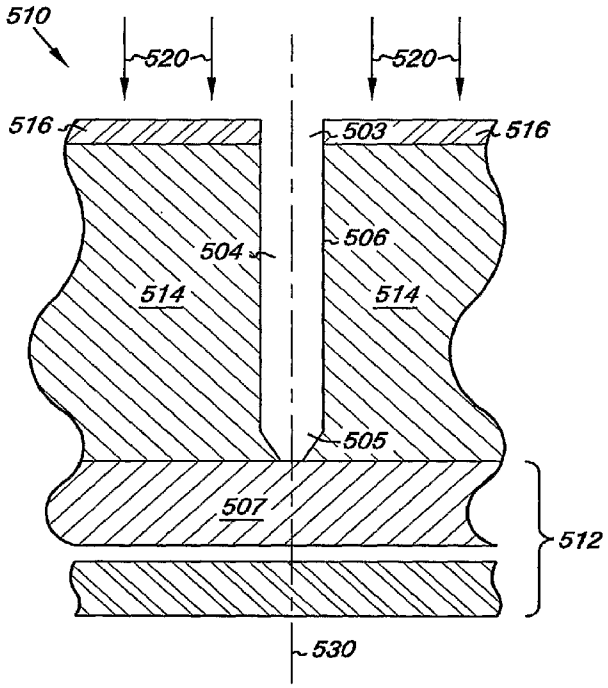
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(57) Abstract: A process for etching a insulating layer to produce an opening having an aspect ratio of at least 15:1 by supplying a first gaseous etchant having at least fifty (50) percent He to a plasma etch reactor, and exposing the insulating layer to a plasma of the first gaseous etchant. Use of the first gaseous etchant reduces the occurrence of twisting in openings in insulating layers having an aspect ratio of at least 15:1.

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